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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	64
Program Memory Size	192KB (192K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 17x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-LFQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f101mhafb-50

○ ROM, RAM capacities

Flash ROM	Data flash	RAM	RL78/G13					
			20 pins	24 pins	25 pins	30 pins	32 pins	36 pins
128 KB	8 KB	12 KB	—	—	—	R5F100AG	R5F100BG	R5F100CG
	—		—	—	—	R5F101AG	R5F101BG	R5F101CG
96 KB	8 KB	8 KB	—	—	—	R5F100AF	R5F100BF	R5F100CF
	—		—	—	—	R5F101AF	R5F101BF	R5F101CF
64 KB	4 KB	4 KB Note	R5F1006E	R5F1007E	R5F1008E	R5F100AE	R5F100BE	R5F100CE
	—		R5F1016E	R5F1017E	R5F1018E	R5F101AE	R5F101BE	R5F101CE
48 KB	4 KB	3 KB Note	R5F1006D	R5F1007D	R5F1008D	R5F100AD	R5F100BD	R5F100CD
	—		R5F1016D	R5F1017D	R5F1018D	R5F101AD	R5F101BD	R5F101CD
32 KB	4 KB	2 KB	R5F1006C	R5F1007C	R5F1008C	R5F100AC	R5F100BC	R5F100CC
	—		R5F1016C	R5F1017C	R5F1018C	R5F101AC	R5F101BC	R5F101CC
16 KB	4 KB	2 KB	R5F1006A	R5F1007A	R5F1008A	R5F100AA	R5F100BA	R5F100CA
	—		R5F1016A	R5F1017A	R5F1018A	R5F101AA	R5F101BA	R5F101CA

Flash ROM	Data flash	RAM	RL78/G13							
			40 pins	44 pins	48 pins	52 pins	64 pins	80 pins	100 pins	128 pins
512 KB	8 KB	32 KB Note	—	R5F100FL	R5F100GL	R5F100JL	R5F100LL	R5F100ML	R5F100PL	R5F100SL
	—		—	R5F101FL	R5F101GL	R5F101JL	R5F101LL	R5F101ML	R5F101PL	R5F101SL
384 KB	8 KB	24 KB	—	R5F100FK	R5F100GK	R5F100JK	R5F100LK	R5F100MK	R5F100PK	R5F100SK
	—		—	R5F101FK	R5F101GK	R5F101JK	R5F101LK	R5F101MK	R5F101PK	R5F101SK
256 KB	8 KB	20 KB Note	—	R5F100FJ	R5F100GJ	R5F100JJ	R5F100LJ	R5F100MJ	R5F100PJ	R5F100SJ
	—		—	R5F101FJ	R5F101GJ	R5F101JJ	R5F101LJ	R5F101MJ	R5F101PJ	R5F101SJ
192 KB	8 KB	16 KB	R5F100EH	R5F100FH	R5F100GH	R5F100JH	R5F100LH	R5F100MH	R5F100PH	R5F100SH
	—		R5F101EH	R5F101FH	R5F101GH	R5F101JH	R5F101LH	R5F101MH	R5F101PH	R5F101SH
128 KB	8 KB	12 KB	R5F100EG	R5F100FG	R5F100GG	R5F100JG	R5F100LG	R5F100MG	R5F100PG	—
	—		R5F101EG	R5F101FG	R5F101GG	R5F101JG	R5F101LG	R5F101MG	R5F101PG	—
96 KB	8 KB	8 KB	R5F100EF	R5F100FF	R5F100GF	R5F100JF	R5F100LF	R5F100MF	R5F100PF	—
	—		R5F101EF	R5F101FF	R5F101GF	R5F101JF	R5F101LF	R5F101MF	R5F101PF	—
64 KB	4 KB	4 KB Note	R5F100EE	R5F100FE	R5F100GE	R5F100JE	R5F100LE	—	—	—
	—		R5F101EE	R5F101FE	R5F101GE	R5F101JE	R5F101LE	—	—	—
48 KB	4 KB	3 KB Note	R5F100ED	R5F100FD	R5F100GD	R5F100JD	R5F100LD	—	—	—
	—		R5F101ED	R5F101FD	R5F101GD	R5F101JD	R5F101LD	—	—	—
32 KB	4 KB	2 KB	R5F100EC	R5F100FC	R5F100GC	R5F100JC	R5F100LC	—	—	—
	—		R5F101EC	R5F101FC	R5F101GC	R5F101JC	R5F101LC	—	—	—
16 KB	4 KB	2 KB	R5F100EA	R5F100FA	R5F100GA	—	—	—	—	—
	—		R5F101EA	R5F101FA	R5F101GA	—	—	—	—	—

Note The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xD, R5F101xD (x = 6 to 8, A to C, E to G, J, L): Start address FF300H

R5F100xE, R5F101xE (x = 6 to 8, A to C, E to G, J, L): Start address FEF00H

R5F100xJ, R5F101xJ (x = F, G, J, L, M, P): Start address FAF00H

R5F100xL, R5F101xL (x = F, G, J, L, M, P, S): Start address F7F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

Table 1-1. List of Ordering Part Numbers

(11/12)

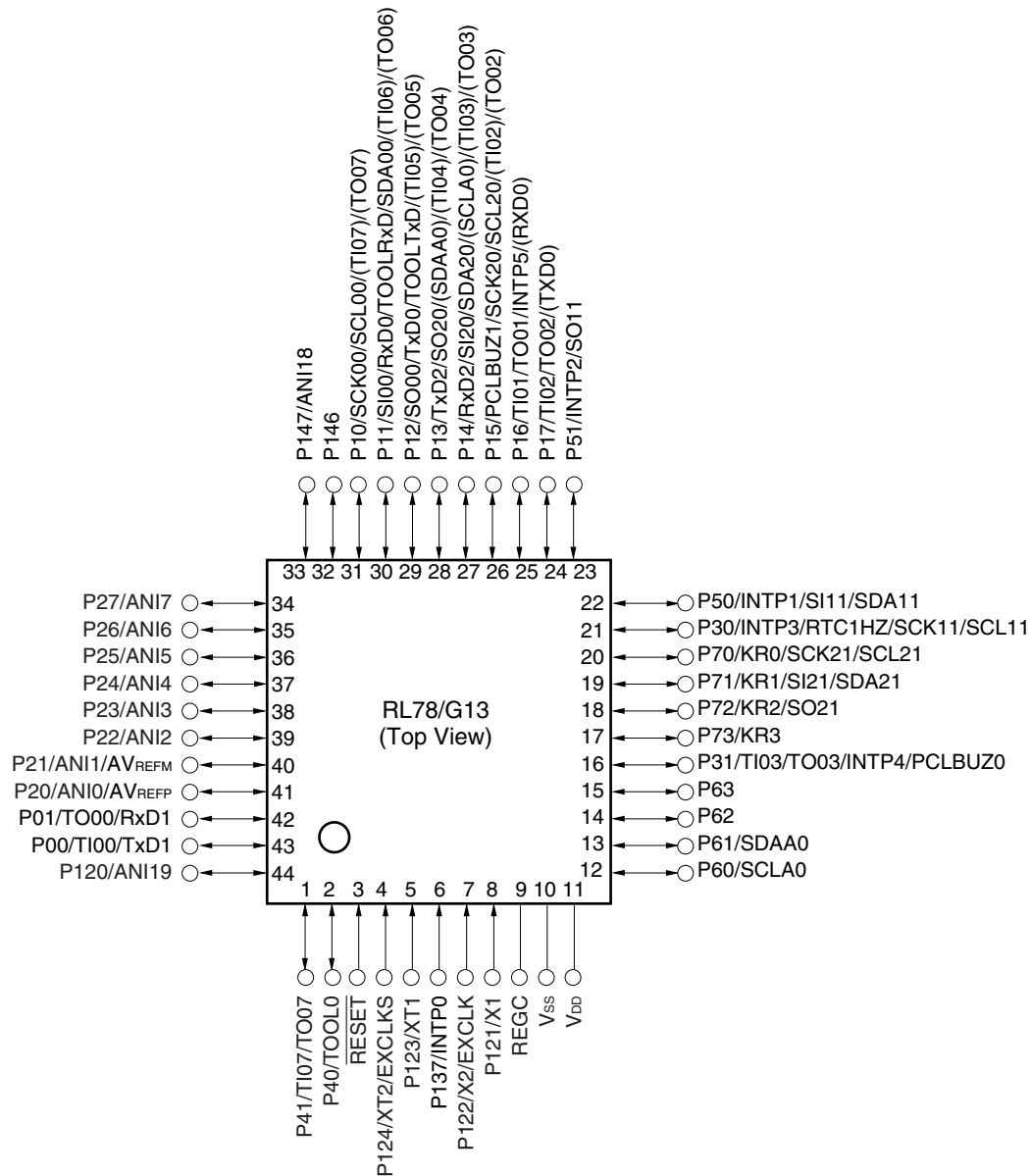
Pin count	Package	Data flash	Fields of Application Note	Ordering Part Number
100 pins	100-pin plastic LFQFP (14 × 14 mm, 0.5 mm pitch)	Mounted	A	R5F100PFAFB#V0, R5F100PGAFA#V0, R5F100PHAFA#V0, R5F100PJAFB#V0, R5F100PKAFB#V0, R5F100PLAFB#V0 R5F100PFAFB#X0, R5F100PGAFA#X0, R5F100PHAFA#X0, R5F100PJAFB#X0, R5F100PKAFB#X0, R5F100PLAFB#X0
			D	R5F100PFDFB#V0, R5F100PGDFB#V0, R5F100PHDFB#V0, R5F100PJDFB#V0, R5F100PKDFB#V0, R5F100PLDFB#V0 R5F100PFDFB#X0, R5F100PGDFB#X0, R5F100PHDFB#X0, R5F100PJDFB#X0, R5F100PKDFB#X0, R5F100PLDFB#X0
			G	R5F100PFGFB#V0, R5F100PGGFB#V0, R5F100PHGFB#V0, R5F100PJGFB#V0 R5F100PFGFB#X0, R5F100PGGFB#X0, R5F100PHGFB#X0, R5F100PJGFB#X0
		Not mounted	A	R5F101PFAFB#V0, R5F101PGAFA#V0, R5F101PHAFA#V0, R5F101PJAFB#V0, R5F101PKAFB#V0, R5F101PLAFB#V0 R5F101PFAFB#X0, R5F101PGAFA#X0, R5F101PHAFA#X0, R5F101PJAFB#X0, R5F101PKAFB#X0, R5F101PLAFB#X0
			D	R5F101PFDFB#V0, R5F101PGDFB#V0, R5F101PHDFB#V0, R5F101PJDFB#V0, R5F101PKDFB#V0, R5F101PLDFB#V0 R5F101PFDFB#X0, R5F101PGDFB#X0, R5F101PHDFB#X0, R5F101PJDFB#X0, R5F101PKDFB#X0, R5F101PLDFB#X0
	100-pin plastic LQFP (14 × 20 mm, 0.65 mm pitch)	Mounted	A	R5F100PFAFA#V0, R5F100PGAFA#V0, R5F100PHAFA#V0, R5F100PJAFB#V0, R5F100PKAFA#V0, R5F100PLAFA#V0 R5F100PFAFA#X0, R5F100PGAFA#X0, R5F100PHAFA#X0, R5F100PJAFB#X0, R5F100PKAFA#X0, R5F100PLAFA#X0
			D	R5F100PFDA#V0, R5F100PGDA#V0, R5F100PHDA#V0, R5F100PJDA#V0, R5F100PKDA#V0, R5F100PLDA#V0 R5F100PFDA#X0, R5F100PGDA#X0, R5F100PHDA#X0, R5F100PJDA#X0, R5F100PKDA#X0, R5F100PLDA#X0
			G	R5F100PFGFA#V0, R5F100PGGFA#V0, R5F100PHGFA#V0, R5F100PJGFA#V0 R5F100PFGFA#X0, R5F100PGGFA#X0, R5F100PHGFA#X0, R5F100PJGFA#X0
		Not mounted	A	R5F101PFAFA#V0, R5F101PGAFA#V0, R5F101PHAFA#V0, R5F101PJAFB#V0, R5F101PKAFA#V0, R5F101PLAFA#V0 R5F101PFAFA#X0, R5F101PGAFA#X0, R5F101PHAFA#X0, R5F101PJAFB#X0, R5F101PKAFA#X0, R5F101PLAFA#X0
			D	R5F101PFDA#V0, R5F101PGDA#V0, R5F101PHDA#V0, R5F101PJDA#V0, R5F101PKDA#V0, R5F101PLDA#V0 R5F101PFDA#X0, R5F101PGDA#X0, R5F101PHDA#X0, R5F101PJDA#X0, R5F101PKDA#X0, R5F101PLDA#X0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3.8 44-pin products

- 44-pin plastic LQFP (10 × 10 mm, 0.8 mm pitch)



Caution Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

[40-pin, 44-pin, 48-pin, 52-pin, 64-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

(1/2)

Item		40-pin		44-pin		48-pin		52-pin		64-pin	
		R5F100Ex	R5F101Ex	R5F100Fx	R5F101Fx	R5F100Gx	R5F101Gx	R5F100Jx	R5F101Jx	R5F100Lx	R5F101Lx
Code flash memory (KB)		16 to 192		16 to 512		16 to 512		32 to 512		32 to 512	
Data flash memory (KB)		4 to 8	—	4 to 8	—	4 to 8	—	4 to 8	—	4 to 8	—
RAM (KB)		2 to 16 ^{Note1}		2 to 32 ^{Note1}		2 to 32 ^{Note1}		2 to 32 ^{Note1}		2 to 32 ^{Note1}	
Address space		1 MB									
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (High-speed main) mode: 1 to 20 MHz (V _{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V _{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V _{DD} = 1.6 to 5.5 V)									
	High-speed on-chip oscillator	HS (High-speed main) mode: 1 to 32 MHz (V _{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V _{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V _{DD} = 1.6 to 5.5 V)									
Subsystem clock		XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz									
Low-speed on-chip oscillator		15 kHz (TYP.)									
General-purpose registers		(8-bit register × 8) × 4 banks									
Minimum instruction execution time		0.03125 μs (High-speed on-chip oscillator: f _{IH} = 32 MHz operation)									
		0.05 μs (High-speed system clock: f _{MX} = 20 MHz operation)									
		30.5 μs (Subsystem clock: f _{SUB} = 32.768 kHz operation)									
Instruction set		• Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.									
I/O port	Total	36		40		44		48		58	
	CMOS I/O	28 (N-ch O.D. I/O [V _{DD} withstand voltage]: 10)		31 (N-ch O.D. I/O [V _{DD} withstand voltage]: 10)		34 (N-ch O.D. I/O [V _{DD} withstand voltage]: 11)		38 (N-ch O.D. I/O [V _{DD} withstand voltage]: 13)		48 (N-ch O.D. I/O [V _{DD} withstand voltage]: 15)	
	CMOS input	5		5		5		5		5	
	CMOS output	—		—		1		1		1	
	N-ch O.D. I/O (withstand voltage: 6 V)	3		4		4		4		4	
Timer	16-bit timer	8 channels									
	Watchdog timer	1 channel									
	Real-time clock (RTC)	1 channel									
	12-bit interval timer (IT)	1 channel									
	Timer output	4 channels (PWM outputs: 3 ^{Note2}), 8 channels (PWM outputs: 7 ^{Note2, Note3})		5 channels (PWM outputs: 4 ^{Note2}), 8 channels (PWM outputs: 7 ^{Note2}) ^{Note3}						8 channels (PWM outputs: 7 ^{Note2})	
	RTC output	1 channel • 1 Hz (subsystem clock: f _{SUB} = 32.768 kHz)									

Notes 1. The flash library uses RAM in self-programming and rewriting of the data flash memory. The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xD, R5F101xD (x = E to G, J, L): Start address FF300H

R5F100xE, R5F101xE (x = E to G, J, L): Start address FEF00H

R5F100xJ, R5F101xJ (x = F, G, J, L): Start address FAF00H

R5F100xL, R5F101xL (x = F, G, J, L): Start address F7F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

2.1 Absolute Maximum Ratings

Absolute Maximum Ratings (T_A = 25°C) (1/2)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	V _{DD}		-0.5 to +6.5	V
	EV _{DD0} , EV _{DD1}	EV _{DD0} = EV _{DD1}	-0.5 to +6.5	V
	EV _{SS0} , EV _{SS1}	EV _{SS0} = EV _{SS1}	-0.5 to +0.3	V
REGC pin input voltage	V _{IREGC}	REGC	-0.3 to +2.8 and -0.3 to V _{DD} + 0.3 ^{Note 1}	V
Input voltage	V _{I1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	-0.3 to EV _{DD0} + 0.3 and -0.3 to V _{DD} + 0.3 ^{Note 2}	V
	V _{I2}	P60 to P63 (N-ch open-drain)	-0.3 to +6.5	V
	V _{I3}	P20 to P27, P121 to P124, P137, P150 to P156, EXCLK, EXCLKS, RESET	-0.3 to V _{DD} + 0.3 ^{Note 2}	V
Output voltage	V _{O1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	-0.3 to EV _{DD0} + 0.3 and -0.3 to V _{DD} + 0.3 ^{Note 2}	V
	V _{O2}	P20 to P27, P150 to P156	-0.3 to V _{DD} + 0.3 ^{Note 2}	V
Analog input voltage	V _{AI1}	ANI16 to ANI26	-0.3 to EV _{DD0} + 0.3 and -0.3 to AV _{REF} (+) + 0.3 ^{Notes 2, 3}	V
	V _{AI2}	ANI0 to ANI14	-0.3 to V _{DD} + 0.3 and -0.3 to AV _{REF} (+) + 0.3 ^{Notes 2, 3}	V

Notes 1. Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μF). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.

2. Must be 6.5 V or lower.

3. Do not exceed AV_{REF}(+) + 0.3 V in case of A/D conversion target pin.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remarks 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2. AV_{REF}(+) : + side reference voltage of the A/D converter.

3. V_{SS} : Reference voltage

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (2/5)

Items	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Output current, low ^{Note 1}	I _{OL1}	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147			20.0 ^{Note 2}	mA
		Per pin for P60 to P63			15.0 ^{Note 2}	mA
		Total of P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145 (When duty ≤ 70% ^{Note 3})	4.0 V ≤ EV _{DD0} ≤ 5.5 V		70.0	mA
			2.7 V ≤ EV _{DD0} < 4.0 V		15.0	mA
			1.8 V ≤ EV _{DD0} < 2.7 V		9.0	mA
			1.6 V ≤ EV _{DD0} < 1.8 V		4.5	mA
		Total of P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147 (When duty ≤ 70% ^{Note 3})	4.0 V ≤ EV _{DD0} ≤ 5.5 V		80.0	mA
			2.7 V ≤ EV _{DD0} < 4.0 V		35.0	mA
			1.8 V ≤ EV _{DD0} < 2.7 V		20.0	mA
			1.6 V ≤ EV _{DD0} < 1.8 V		10.0	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})			150.0	mA
	I _{OL2}	Per pin for P20 to P27, P150 to P156			0.4 ^{Note 2}	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	1.6 V ≤ V _{DD} ≤ 5.5 V		5.0	mA

- Notes**
- Value of current at which the device operation is guaranteed even if the current flows from an output pin to the EV_{SS0}, EV_{SS1} and V_{SS} pin.
 - However, do not exceed the total current value.
 - Specification under conditions where the duty factor ≤ 70%.
The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).
 - Total output current of pins = (I_{OL} × 0.7)/(n × 0.01)

<Example> Where n = 80% and I_{OL} = 10.0 mA

Total output current of pins = (10.0 × 0.7)/(80 × 0.01) ≅ 8.7 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products**(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (1/2)**

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current Note 1	I _{DD1}	Operating mode	HS (high-speed main) mode Note 5	f _{IH} = 32 MHz Note 3	Basic operation	V _{DD} = 5.0 V		2.3		mA
						V _{DD} = 3.0 V		2.3		mA
					Normal operation	V _{DD} = 5.0 V		5.2	8.5	mA
						V _{DD} = 3.0 V		5.2	8.5	mA
				f _{IH} = 24 MHz Note 3	Normal operation	V _{DD} = 5.0 V		4.1	6.6	mA
						V _{DD} = 3.0 V		4.1	6.6	mA
				f _{IH} = 16 MHz Note 3	Normal operation	V _{DD} = 5.0 V		3.0	4.7	mA
						V _{DD} = 3.0 V		3.0	4.7	mA
			LS (low-speed main) mode Note 5	f _{IH} = 8 MHz Note 3	Normal operation	V _{DD} = 3.0 V		1.3	2.1	mA
						V _{DD} = 2.0 V		1.3	2.1	mA
			LV (low-voltage main) mode Note 5	f _{IH} = 4 MHz Note 3	Normal operation	V _{DD} = 3.0 V		1.3	1.8	mA
						V _{DD} = 2.0 V		1.3	1.8	mA
			HS (high-speed main) mode Note 5	f _{MX} = 20 MHz Note 2, V _{DD} = 5.0 V	Normal operation	Square wave input		3.4	5.5	mA
						Resonator connection		3.6	5.7	mA
				f _{MX} = 20 MHz Note 2, V _{DD} = 3.0 V	Normal operation	Square wave input		3.4	5.5	mA
						Resonator connection		3.6	5.7	mA
				f _{MX} = 10 MHz Note 2, V _{DD} = 5.0 V	Normal operation	Square wave input		2.1	3.2	mA
						Resonator connection		2.1	3.2	mA
				f _{MX} = 10 MHz Note 2, V _{DD} = 3.0 V	Normal operation	Square wave input		2.1	3.2	mA
						Resonator connection		2.1	3.2	mA
			LS (low-speed main) mode Note 5	f _{MX} = 8 MHz Note 2, V _{DD} = 3.0 V	Normal operation	Square wave input		1.2	2.0	mA
						Resonator connection		1.2	2.0	mA
				f _{MX} = 8 MHz Note 2, V _{DD} = 2.0 V	Normal operation	Square wave input		1.2	2.0	mA
						Resonator connection		1.2	2.0	mA
			Subsystem clock operation	f _{SUB} = 32.768 kHz Note 4 T _A = -40°C	Normal operation	Square wave input		4.8	5.9	μA
						Resonator connection		4.9	6.0	μA
				f _{SUB} = 32.768 kHz Note 4 T _A = +25°C	Normal operation	Square wave input		4.9	5.9	μA
						Resonator connection		5.0	6.0	μA
				f _{SUB} = 32.768 kHz Note 4 T _A = +50°C	Normal operation	Square wave input		5.0	7.6	μA
						Resonator connection		5.1	7.7	μA
				f _{SUB} = 32.768 kHz Note 4 T _A = +70°C	Normal operation	Square wave input		5.2	9.3	μA
						Resonator connection		5.3	9.4	μA
				f _{SUB} = 32.768 kHz Note 4 T _A = +85°C	Normal operation	Square wave input		5.7	13.3	μA
						Resonator connection		5.8	13.4	μA

(Notes and Remarks are listed on the next page.)

- Remarks 1.** f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
2. f_{IH}: High-speed on-chip oscillator clock frequency
3. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)
4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is T_A = 25°C

(4) Peripheral Functions (Common to all products)**(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)**

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscillator operating current	I _{FIL} ^{Note 1}				0.20		μA
RTC operating current	I _{RTC} ^{Notes 1, 2, 3}				0.02		μA
12-bit interval timer operating current	I _{IT} ^{Notes 1, 2, 4}				0.02		μA
Watchdog timer operating current	I _{WDT} ^{Notes 1, 2, 5}	f _{IL} = 15 kHz			0.22		μA
A/D converter operating current	I _{ADC} ^{Notes 1, 6}	When conversion at maximum speed	Normal mode, AV _{REFP} = V _{DD} = 5.0 V		1.3	1.7	mA
			Low voltage mode, AV _{REFP} = V _{DD} = 3.0 V		0.5	0.7	mA
A/D converter reference voltage current	I _{ADREF} ^{Note 1}				75.0		μA
Temperature sensor operating current	I _{TMPS} ^{Note 1}				75.0		μA
LVD operating current	I _{LVI} ^{Notes 1, 7}				0.08		μA
Self-programming operating current	I _{FSP} ^{Notes 1, 9}				2.50	12.20	mA
BGO operating current	I _{BGO} ^{Notes 1, 8}				2.50	12.20	mA
SNOOZE operating current	I _{SNOZ} ^{Note 1}	ADC operation	The mode is performed ^{Note 10}		0.50	0.60	mA
			The A/D conversion operations are performed, Low voltage mode, AV _{REFP} = V _{DD} = 3.0 V		1.20	1.44	mA
		CSI/UART operation			0.70	0.84	mA

Notes 1. Current flowing to V_{DD}.

- When high speed on-chip oscillator and high-speed system clock are stopped.
- Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either I_{DD1} or I_{DD2}, and I_{RTC}, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added. I_{DD2} subsystem clock operation includes the operational current of the real-time clock.
- Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either I_{DD1} or I_{DD2}, and I_{IT}, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added.
- Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{WDT} when the watchdog timer is in operation.

2.4 AC Characteristics

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	T _{CY}	Main system clock (f _{MAIN}) operation	HS (high-speed main) mode	2.7 V ≤ V _{DD} ≤ 5.5 V	0.03125	1	μs
				2.4 V ≤ V _{DD} < 2.7 V	0.0625	1	μs
			LS (low-speed main) mode	1.8 V ≤ V _{DD} ≤ 5.5 V	0.125	1	μs
			LV (low-voltage main) mode	1.6 V ≤ V _{DD} ≤ 5.5 V	0.25	1	μs
		Subsystem clock (f _{SUB}) operation		1.8 V ≤ V _{DD} ≤ 5.5 V	28.5	30.5	31.3 μs
		In the self programming mode	HS (high-speed main) mode	2.7 V ≤ V _{DD} ≤ 5.5 V	0.03125	1	μs
				2.4 V ≤ V _{DD} < 2.7 V	0.0625	1	μs
			LS (low-speed main) mode	1.8 V ≤ V _{DD} ≤ 5.5 V	0.125	1	μs
			LV (low-voltage main) mode	1.8 V ≤ V _{DD} ≤ 5.5 V	0.25	1	μs
External system clock frequency	f _{EX}	2.7 V ≤ V _{DD} ≤ 5.5 V		1.0		20.0	MHz
		2.4 V ≤ V _{DD} < 2.7 V		1.0		16.0	MHz
		1.8 V ≤ V _{DD} < 2.4 V		1.0		8.0	MHz
		1.6 V ≤ V _{DD} < 1.8 V		1.0		4.0	MHz
	f _{EXS}			32		35	kHz
External system clock input high-level width, low-level width	t _{EXH} , t _{EXL}	2.7 V ≤ V _{DD} ≤ 5.5 V		24			ns
		2.4 V ≤ V _{DD} < 2.7 V		30			ns
		1.8 V ≤ V _{DD} < 2.4 V		60			ns
		1.6 V ≤ V _{DD} < 1.8 V		120			ns
	t _{EXHS} , t _{EXLS}			13.7			μs
Ti00 to Ti07, Ti10 to Ti17 input high-level width, low-level width	t _{TIH} , t _{TIL}			1/f _{MCK} +10			ns ^{Note}
TO00 to TO07, TO10 to TO17 output frequency	f _{TO}	HS (high-speed main) mode		4.0 V ≤ EV _{DD0} ≤ 5.5 V		16	MHz
				2.7 V ≤ EV _{DD0} < 4.0 V		8	MHz
				1.8 V ≤ EV _{DD0} < 2.7 V		4	MHz
				1.6 V ≤ EV _{DD0} < 1.8 V		2	MHz
		LS (low-speed main) mode		1.8 V ≤ EV _{DD0} ≤ 5.5 V		4	MHz
				1.6 V ≤ EV _{DD0} < 1.8 V		2	MHz
		LV (low-voltage main) mode		1.6 V ≤ EV _{DD0} ≤ 5.5 V		2	MHz
PCLBUZ0, PCLBUZ1 output frequency	f _{PCL}	HS (high-speed main) mode		4.0 V ≤ EV _{DD0} ≤ 5.5 V		16	MHz
				2.7 V ≤ EV _{DD0} < 4.0 V		8	MHz
				1.8 V ≤ EV _{DD0} < 2.7 V		4	MHz
				1.6 V ≤ EV _{DD0} < 1.8 V		2	MHz
		LS (low-speed main) mode		1.8 V ≤ EV _{DD0} ≤ 5.5 V		4	MHz
				1.6 V ≤ EV _{DD0} < 1.8 V		2	MHz
		LV (low-voltage main) mode		1.8 V ≤ EV _{DD0} ≤ 5.5 V		4	MHz
				1.6 V ≤ EV _{DD0} < 1.8 V		2	MHz
Interrupt input high-level width, low-level width	t _{INTH} , t _{INTL}	INTP0	1.6 V ≤ V _{DD} ≤ 5.5 V	1			μs
		INTP1 to INTP11	1.6 V ≤ EV _{DD0} ≤ 5.5 V	1			μs
Key interrupt input low-level width	t _{KR}	KR0 to KR7	1.8 V ≤ EV _{DD0} ≤ 5.5 V	250			ns
			1.6 V ≤ EV _{DD0} < 1.8 V	1			μs
RESET low-level width	t _{RSL}			10			μs

(Note and Remark are listed on the next page.)

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (2/2)

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Slp setup time (to SCKp↑) ^{Note 1}	t _{SIK2}	2.7 V ≤ EV _{DD0} ≤ 5.5 V		1/f _{MCK} +20		1/f _{MCK} +30		1/f _{MCK} +30		ns
		1.8 V ≤ EV _{DD0} ≤ 5.5 V		1/f _{MCK} +30		1/f _{MCK} +30		1/f _{MCK} +30		ns
		1.7 V ≤ EV _{DD0} ≤ 5.5 V		1/f _{MCK} +40		1/f _{MCK} +40		1/f _{MCK} +40		ns
		1.6 V ≤ EV _{DD0} ≤ 5.5 V		—		1/f _{MCK} +40		1/f _{MCK} +40		ns
Slp hold time (from SCKp↑) ^{Note 2}	t _{KSI2}	1.8 V ≤ EV _{DD0} ≤ 5.5 V		1/f _{MCK} +31		1/f _{MCK} +31		1/f _{MCK} +31		ns
		1.7 V ≤ EV _{DD0} ≤ 5.5 V		1/f _{MCK} +250		1/f _{MCK} +250		1/f _{MCK} +250		ns
		1.6 V ≤ EV _{DD0} ≤ 5.5 V		—		1/f _{MCK} +250		1/f _{MCK} +250		ns
Delay time from SCKp↓ to SOp output ^{Note 3}	t _{KSO2}	C = 30 pF ^{Note 4}	2.7 V ≤ EV _{DD0} ≤ 5.5 V		2/f _{MCK} +44		2/f _{MCK} +110		2/f _{MCK} +110	ns
			2.4 V ≤ EV _{DD0} ≤ 5.5 V		2/f _{MCK} +75		2/f _{MCK} +110		2/f _{MCK} +110	ns
			1.8 V ≤ EV _{DD0} ≤ 5.5 V		2/f _{MCK} +110		2/f _{MCK} +110		2/f _{MCK} +110	ns
			1.7 V ≤ EV _{DD0} ≤ 5.5 V		2/f _{MCK} +220		2/f _{MCK} +220		2/f _{MCK} +220	ns
			1.6 V ≤ EV _{DD0} ≤ 5.5 V		—		2/f _{MCK} +220		2/f _{MCK} +220	ns

- Notes**
1. When DAP_{mn} = 0 and CKP_{mn} = 0, or DAP_{mn} = 1 and CKP_{mn} = 1. The Slp setup time becomes “to SCKp↓” when DAP_{mn} = 0 and CKP_{mn} = 1, or DAP_{mn} = 1 and CKP_{mn} = 0.
 2. When DAP_{mn} = 0 and CKP_{mn} = 0, or DAP_{mn} = 1 and CKP_{mn} = 1. The Slp hold time becomes “from SCKp↓” when DAP_{mn} = 0 and CKP_{mn} = 1, or DAP_{mn} = 1 and CKP_{mn} = 0.
 3. When DAP_{mn} = 0 and CKP_{mn} = 0, or DAP_{mn} = 1 and CKP_{mn} = 1. The delay time to SOp output becomes “from SCKp↑” when DAP_{mn} = 0 and CKP_{mn} = 1, or DAP_{mn} = 1 and CKP_{mn} = 0.
 4. C is the load capacitance of the SOp output lines.
 5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

Caution Select the normal input buffer for the Slp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- Remarks**
1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1),
n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 4, 5, 8, 14)
 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKS_{mn} bit of serial mode register mn (SMR_{mn}). m: Unit number,
n: Channel number (mn = 00 to 03, 10 to 13))

(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)**(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (2/2)**

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp high-/low-level width	t _{KH2} , t _{KL2}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V	t _{KCY2} /2 - 12		t _{KCY2} /2 - 50		t _{KCY2} /2 - 50		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V	t _{KCY2} /2 - 18		t _{KCY2} /2 - 50		t _{KCY2} /2 - 50		ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2}	t _{KCY2} /2 - 50		t _{KCY2} /2 - 50		t _{KCY2} /2 - 50		ns
Slp setup time (to SCKp↑) ^{Note 3}	t _{SIK2}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V	1/f _{MCK} + 20		1/f _{MCK} + 30		1/f _{MCK} + 30		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V	1/f _{MCK} + 20		1/f _{MCK} + 30		1/f _{MCK} + 30		ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2}	1/f _{MCK} + 30		1/f _{MCK} + 30		1/f _{MCK} + 30		ns
Slp hold time (from SCKp↑) ^{Note 4}	t _{KS12}		1/f _{MCK} + 31		1/f _{MCK} + 31		1/f _{MCK} + 31		ns
Delay time from SCKp↓ to SOp output ^{Note 5}	t _{KSO2}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ		2/f _{MCK} + 120		2/f _{MCK} + 573		2/f _{MCK} + 573	ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ		2/f _{MCK} + 214		2/f _{MCK} + 573		2/f _{MCK} + 573	ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2} , C _b = 30 pF, R _b = 5.5 kΩ		2/f _{MCK} + 573		2/f _{MCK} + 573		2/f _{MCK} + 573	ns

Notes 1. Transfer rate in the SNOOZE mode : MAX. 1 Mbps2. Use it with EV_{DD0} ≥ V_b.

3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the Slp pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Input channel	Reference Voltage		
	Reference voltage (+) = AV _{REFP} Reference voltage (-) = AV _{REFM}	Reference voltage (+) = V _{DD} Reference voltage (-) = V _{SS}	Reference voltage (+) = V _{BGR} Reference voltage (-) = AV _{REFM}
ANI0 to ANI14	Refer to 2.6.1 (1).	Refer to 2.6.1 (3).	Refer to 2.6.1 (4).
ANI16 to ANI26	Refer to 2.6.1 (2).		
Internal reference voltage Temperature sensor output voltage	Refer to 2.6.1 (1).		—

(1) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin : ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage

(T_A = -40 to +85°C, 1.6 V ≤ AV_{REFP} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (-) = AV_{REFM} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES		8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	1.8 V ≤ AV _{REFP} ≤ 5.5 V	1.2	±3.5	LSB
			1.6 V ≤ AV _{REFP} ≤ 5.5 V ^{Note 4}	1.2	±7.0	LSB
Conversion time	t _{CONV}	10-bit resolution Target pin: ANI2 to ANI14	3.6 V ≤ V _{DD} ≤ 5.5 V	2.125	39	μs
			2.7 V ≤ V _{DD} ≤ 5.5 V	3.1875	39	μs
			1.8 V ≤ V _{DD} ≤ 5.5 V	17	39	μs
			1.6 V ≤ V _{DD} ≤ 5.5 V	57	95	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V _{DD} ≤ 5.5 V	2.375	39	μs
			2.7 V ≤ V _{DD} ≤ 5.5 V	3.5625	39	μs
			2.4 V ≤ V _{DD} ≤ 5.5 V	17	39	μs
Zero-scale error ^{Notes 1, 2}	E _{ZS}	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	1.8 V ≤ AV _{REFP} ≤ 5.5 V		±0.25	%FSR
			1.6 V ≤ AV _{REFP} ≤ 5.5 V ^{Note 4}		±0.50	%FSR
Full-scale error ^{Notes 1, 2}	E _{FS}	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	1.8 V ≤ AV _{REFP} ≤ 5.5 V		±0.25	%FSR
			1.6 V ≤ AV _{REFP} ≤ 5.5 V ^{Note 4}		±0.50	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	1.8 V ≤ AV _{REFP} ≤ 5.5 V		±2.5	LSB
			1.6 V ≤ AV _{REFP} ≤ 5.5 V ^{Note 4}		±5.0	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	1.8 V ≤ AV _{REFP} ≤ 5.5 V		±1.5	LSB
			1.6 V ≤ AV _{REFP} ≤ 5.5 V ^{Note 4}		±2.0	LSB
Analog input voltage	V _{AIN}	ANI2 to ANI14	0		AV _{REFP}	V
		Internal reference voltage (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-speed main) mode)	V _{BGR} ^{Note 5}			V
		Temperature sensor output voltage (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-speed main) mode)	V _{TMPS25} ^{Note 5}			V

(Notes are listed on the next page.)

2.6.4 LVD circuit characteristics

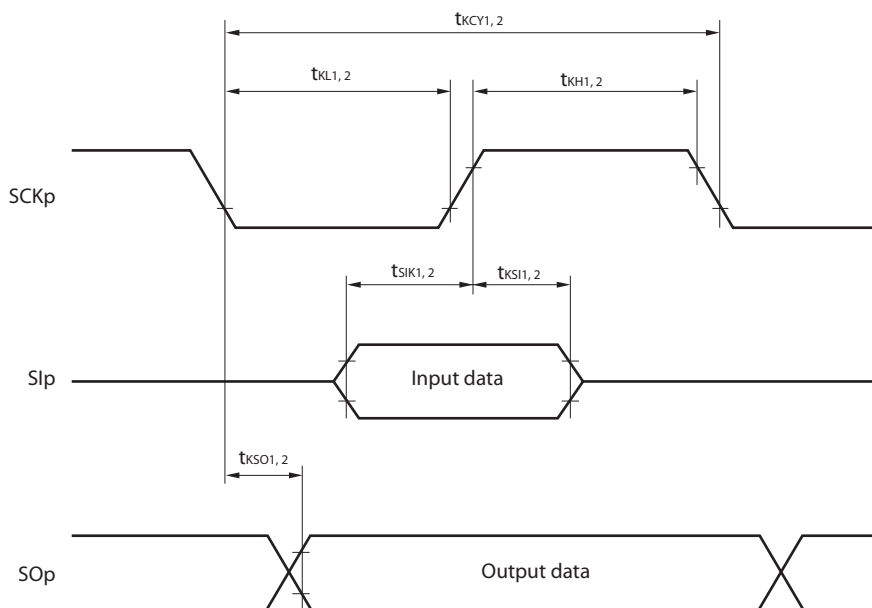
LVD Detection Voltage of Reset Mode and Interrupt Mode(T_A = -40 to +85°C, V_{PDR} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	Supply voltage level	V _{LVD0}	Power supply rise time	3.98	4.06	4.14	V
			Power supply fall time	3.90	3.98	4.06	V
		V _{LVD1}	Power supply rise time	3.68	3.75	3.82	V
			Power supply fall time	3.60	3.67	3.74	V
		V _{LVD2}	Power supply rise time	3.07	3.13	3.19	V
			Power supply fall time	3.00	3.06	3.12	V
		V _{LVD3}	Power supply rise time	2.96	3.02	3.08	V
			Power supply fall time	2.90	2.96	3.02	V
		V _{LVD4}	Power supply rise time	2.86	2.92	2.97	V
			Power supply fall time	2.80	2.86	2.91	V
		V _{LVD5}	Power supply rise time	2.76	2.81	2.87	V
			Power supply fall time	2.70	2.75	2.81	V
		V _{LVD6}	Power supply rise time	2.66	2.71	2.76	V
			Power supply fall time	2.60	2.65	2.70	V
		V _{LVD7}	Power supply rise time	2.56	2.61	2.66	V
			Power supply fall time	2.50	2.55	2.60	V
		V _{LVD8}	Power supply rise time	2.45	2.50	2.55	V
			Power supply fall time	2.40	2.45	2.50	V
		V _{LVD9}	Power supply rise time	2.05	2.09	2.13	V
			Power supply fall time	2.00	2.04	2.08	V
		V _{LVD10}	Power supply rise time	1.94	1.98	2.02	V
			Power supply fall time	1.90	1.94	1.98	V
		V _{LVD11}	Power supply rise time	1.84	1.88	1.91	V
			Power supply fall time	1.80	1.84	1.87	V
		V _{LVD12}	Power supply rise time	1.74	1.77	1.81	V
			Power supply fall time	1.70	1.73	1.77	V
		V _{LVD13}	Power supply rise time	1.64	1.67	1.70	V
			Power supply fall time	1.60	1.63	1.66	V
Minimum pulse width		t _{LW}		300			μs
Detection delay time						300	μs

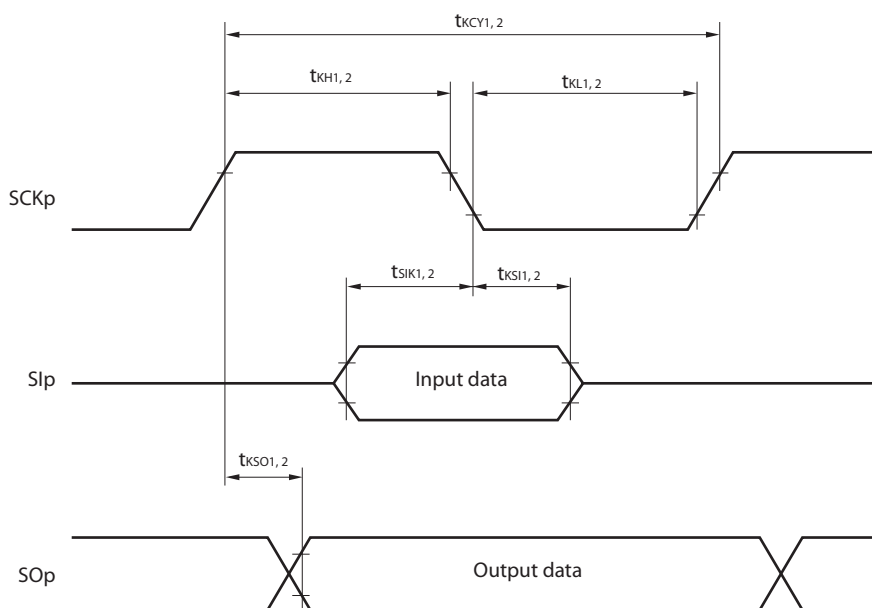
LVD Detection Voltage of Interrupt & Reset Mode(T_A = -40 to +85°C, V_{PDR} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Interrupt and reset mode	VLVDA0	V _{POC2} , V _{POC1} , V _{POC0} = 0, 0, 0, falling reset voltage		1.60	1.63	1.66	V
	VLVDA1	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.74	1.77	1.81	V
			Falling interrupt voltage	1.70	1.73	1.77	V
	VLVDA2	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	1.84	1.88	1.91	V
			Falling interrupt voltage	1.80	1.84	1.87	V
	VLVDA3	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	2.86	2.92	2.97	V
			Falling interrupt voltage	2.80	2.86	2.91	V
	VLVDB0	V _{POC2} , V _{POC1} , V _{POC0} = 0, 0, 1, falling reset voltage		1.80	1.84	1.87	V
	VLVDB1	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.94	1.98	2.02	V
			Falling interrupt voltage	1.90	1.94	1.98	V
	VLVDB2	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.05	2.09	2.13	V
			Falling interrupt voltage	2.00	2.04	2.08	V
	VLVDB3	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.07	3.13	3.19	V
			Falling interrupt voltage	3.00	3.06	3.12	V
	VLVDC0	V _{POC2} , V _{POC1} , V _{POC0} = 0, 1, 0, falling reset voltage		2.40	2.45	2.50	V
	VLVDC1	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.56	2.61	2.66	V
			Falling interrupt voltage	2.50	2.55	2.60	V
	VLVDC2	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.66	2.71	2.76	V
			Falling interrupt voltage	2.60	2.65	2.70	V
	VLVDC3	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.68	3.75	3.82	V
			Falling interrupt voltage	3.60	3.67	3.74	V
	VLVDD0	V _{POC2} , V _{POC1} , V _{POC0} = 0, 1, 1, falling reset voltage		2.70	2.75	2.81	V
	VLVDD1	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.86	2.92	2.97	V
			Falling interrupt voltage	2.80	2.86	2.91	V
	VLVDD2	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.96	3.02	3.08	V
			Falling interrupt voltage	2.90	2.96	3.02	V
	VLVDD3	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.98	4.06	4.14	V
			Falling interrupt voltage	3.90	3.98	4.06	V

CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



- Remarks**
1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31)
 2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (2/3)**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS}0} = \text{EV}_{\text{SS}1} = 0\text{ V}$)**

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
Slp setup time (to SCKp $\uparrow$) ^{Note}	$t_{\text{SIK}1}$	$4.0\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 1.4\text{ k}\Omega$	162		ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD}0} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 2.7\text{ k}\Omega$	354		ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD}0} < 3.3\text{ V}$, $1.6\text{ V} \leq \text{V}_b \leq 2.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 5.5\text{ k}\Omega$	958		ns
Slp hold time (from SCKp $\uparrow$) ^{Note}	$t_{\text{KSI}1}$	$4.0\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 1.4\text{ k}\Omega$	38		ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD}0} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 2.7\text{ k}\Omega$	38		ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD}0} < 3.3\text{ V}$, $1.6\text{ V} \leq \text{V}_b \leq 2.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 2.7\text{ k}\Omega$	38		ns
Delay time from SCKp $\downarrow$ to SOp output ^{Note}	$t_{\text{KSO}1}$	$4.0\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 1.4\text{ k}\Omega$		200	ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD}0} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 2.7\text{ k}\Omega$		390	ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD}0} < 3.3\text{ V}$, $1.6\text{ V} \leq \text{V}_b \leq 2.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 5.5\text{ k}\Omega$		966	ns

Note When $\text{DAPmn} = 0$ and $\text{CKPmn} = 0$, or $\text{DAPmn} = 1$ and $\text{CKPmn} = 1$.

Caution Select the TTL input buffer for the Slp pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/ EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)

(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (–) = V_{SS} (ADREFM = 0), target pin : ANI0 to ANI14, ANI16 to ANI26, internal reference voltage, and temperature sensor output voltage

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\text{ V}$, Reference voltage (+) = V_{DD} , Reference voltage (–) = V_{SS})

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$		1.2	± 7.0	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI0 to ANI14, ANI16 to ANI26	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.125		39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.1875		39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17		39	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.375		39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.5625		39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17		39	μs
Zero-scale error ^{Notes 1, 2}	E _{ZS}	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 0.60	%FSR
Full-scale error ^{Notes 1, 2}	E _{FS}	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 0.60	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 4.0	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 2.0	LSB
Analog input voltage	V_{AIN}	ANI0 to ANI14		0		V_{DD}	V
		ANI16 to ANI26		0		EV_{DD0}	V
		Internal reference voltage output ($2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, HS (high-speed main) mode)		V_{BGR} ^{Note 3}			V
		Temperature sensor output voltage ($2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, HS (high-speed main) mode)		V_{TMPS25} ^{Note 3}			V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. Refer to **3.6.2 Temperature sensor/internal reference voltage characteristics**.

3.6.5 Power supply voltage rising slope characteristics

 $(T_A = -40$ to $+105^\circ\text{C}$, $V_{SS} = 0$ V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	S_{VDD}				54	V/ms

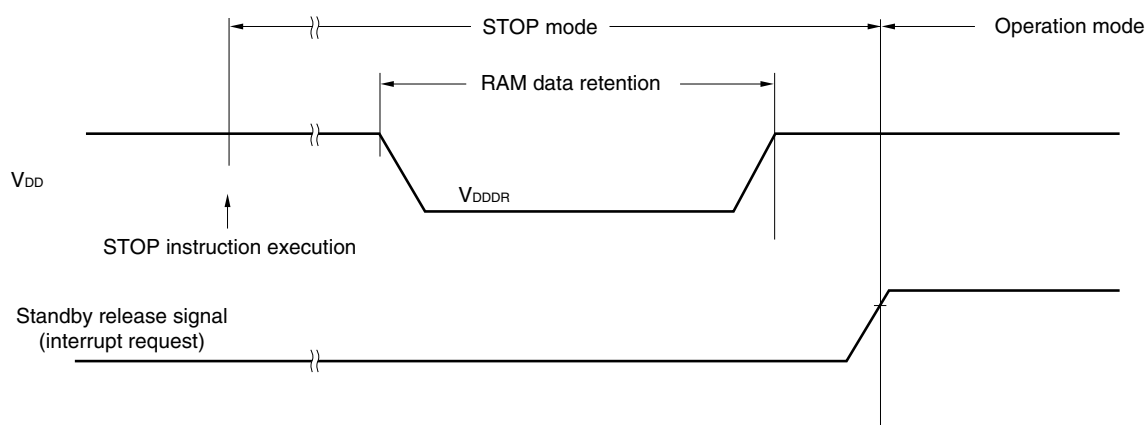
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 3.4 AC Characteristics.

3.7 RAM Data Retention Characteristics

 $(T_A = -40$ to $+105^\circ\text{C}$, $V_{SS} = 0$ V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{DDDR}		1.44 ^{Note}		5.5	V

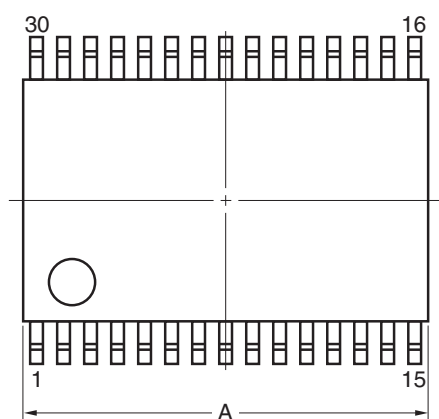
Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



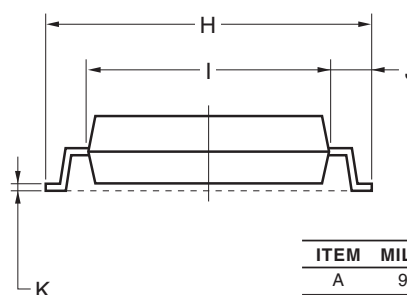
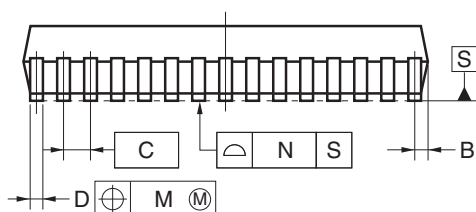
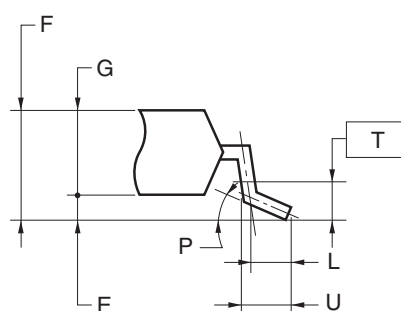
4.4 30-pin Products

R5F100AAASP, R5F100ACASP, R5F100ADASP, R5F100AEASP, R5F100AFASP, R5F100AGASP
 R5F101AAASP, R5F101ACASP, R5F101ADASP, R5F101AEASP, R5F101AFASP, R5F101AGASP
 R5F100AADSP, R5F100ACDSP, R5F100ADDSP, R5F100AEDSP, R5F100AFDSP, R5F100AGDSP
 R5F101AADSP, R5F101ACDSP, R5F101ADDSP, R5F101AEDSP, R5F101AFDSP, R5F101AGDSP
 R5F100AAGSP, R5F100ACGSP, R5F100ADGSP, R5F100AEGSP, R5F100AFGSP, R5F100AGGSP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP30-0300-0.65	PLSP0030JB-B	S30MC-65-5A4-3	0.18



detail of lead end

**NOTE**

Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
A	9.85±0.15
B	0.45 MAX.
C	0.65 (T.P.)
D	0.24 ^{+0.08} _{-0.07}
E	0.1±0.05
F	1.3±0.1
G	1.2
H	8.1±0.2
I	6.1±0.2
J	1.0±0.2
K	0.17±0.03
L	0.5
M	0.13
N	0.10
P	3° ^{+5°} _{-3°}
T	0.25
U	0.6±0.15